

**FIG. 1**

A cross-sectional diagram of a semiconductor device assembly. A substrate 100 is shown at the top. Below it is a layer 128. A central feature 120 is formed in layer 128, containing a core 126. On either side of core 126 are regions 124 and 122. Below these is a layer 114. At the bottom is a multi-layered stack 104, which includes layers 108, 102, 112, 106a, 106b, and 106c.

128 {  
 132 {  
 124 {

Sn  
 intermetallic  
 Mo  
 SiO<sub>2</sub>/Ti  
 Si

6.12 μm  
 1.53 μm  
 1.28 μm  
 8.90 μm

134 ←

001-10 7.0kV 0.0mm x7.00k YAGBSE 10/29/2003 12:39 4.29 μm

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FIG. 3

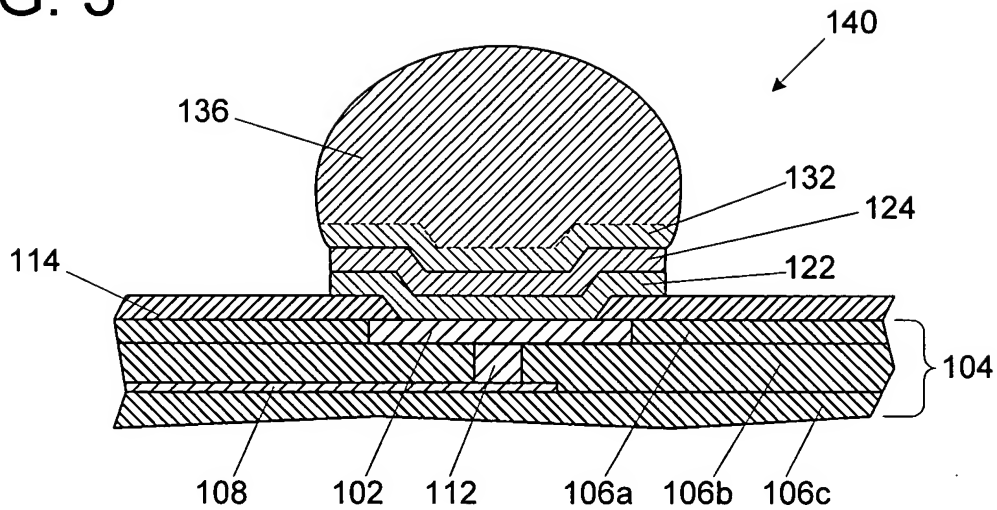


FIG. 4

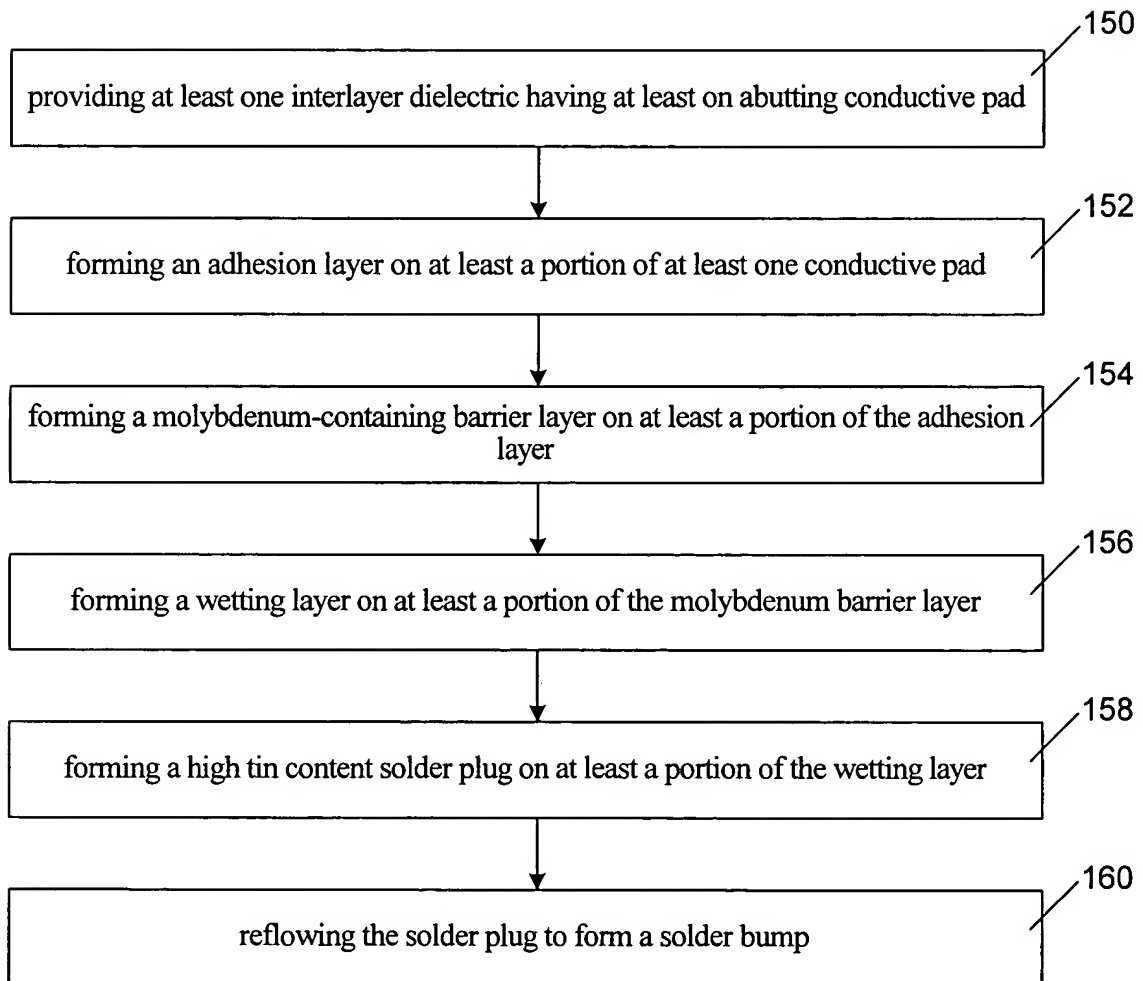


FIG. 5

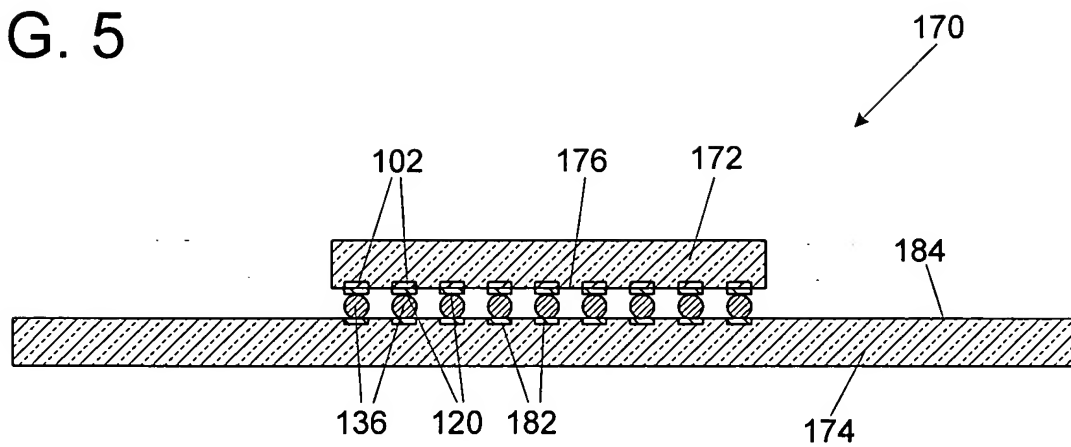


FIG. 6

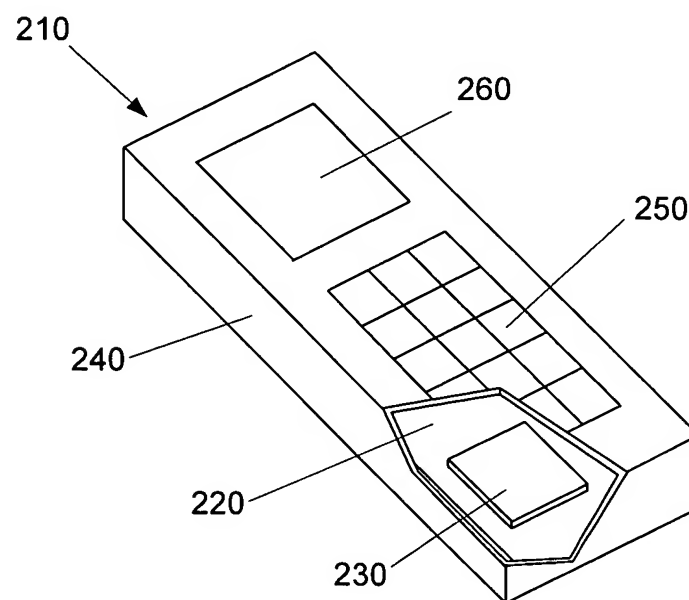


FIG. 7

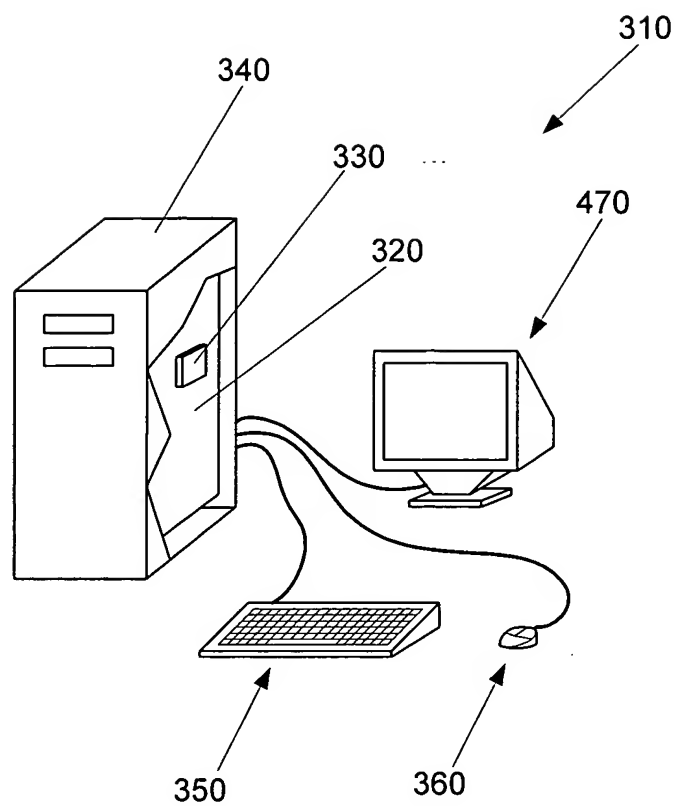


FIG. 8  
Prior Art

